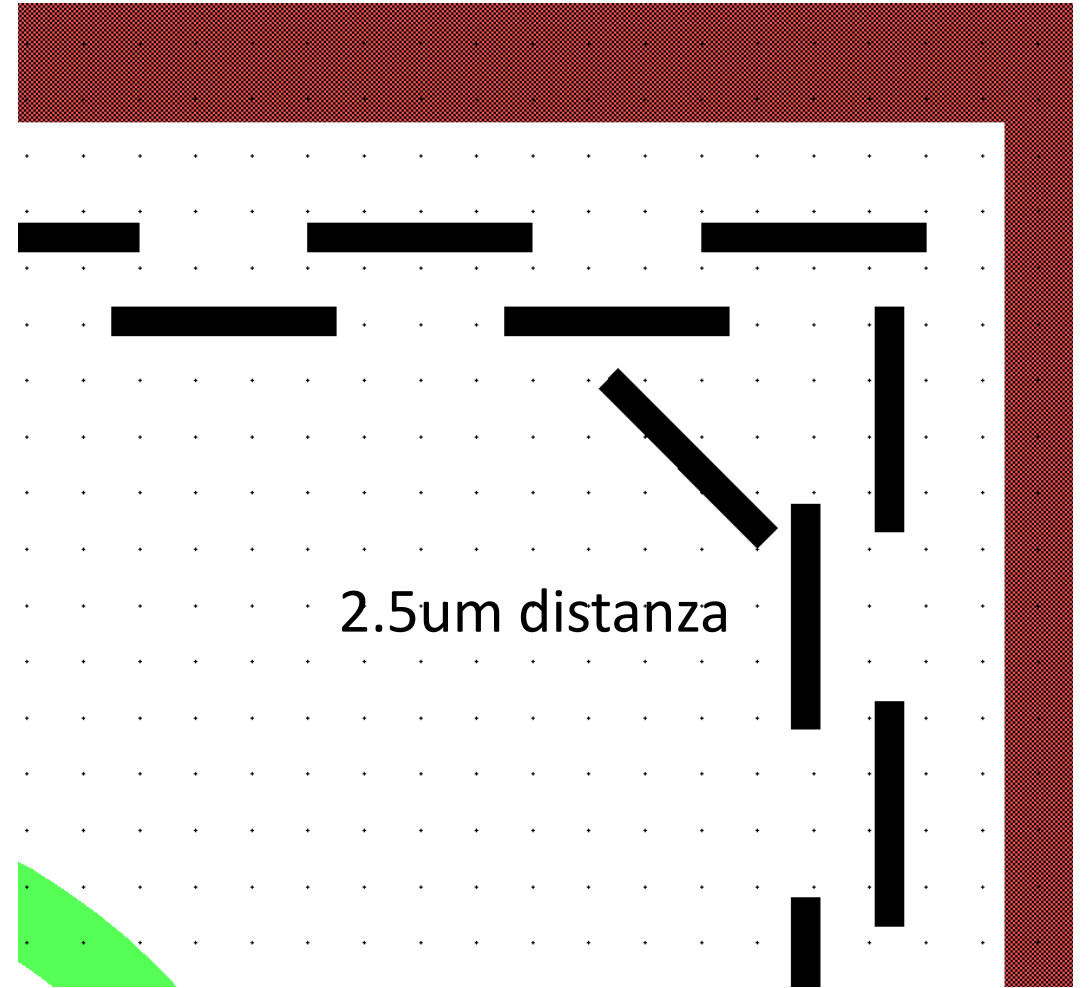


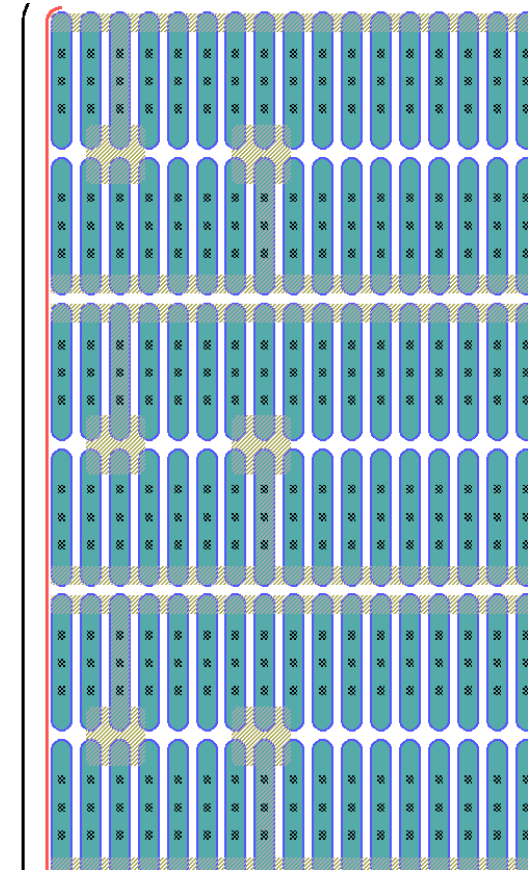
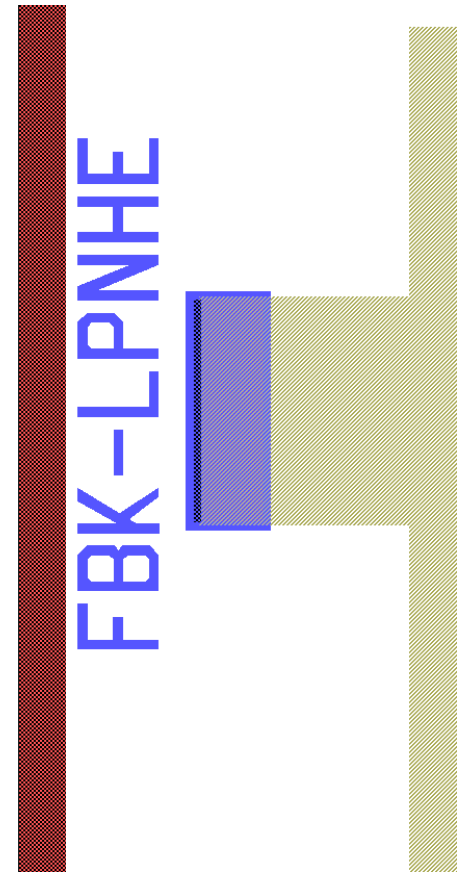
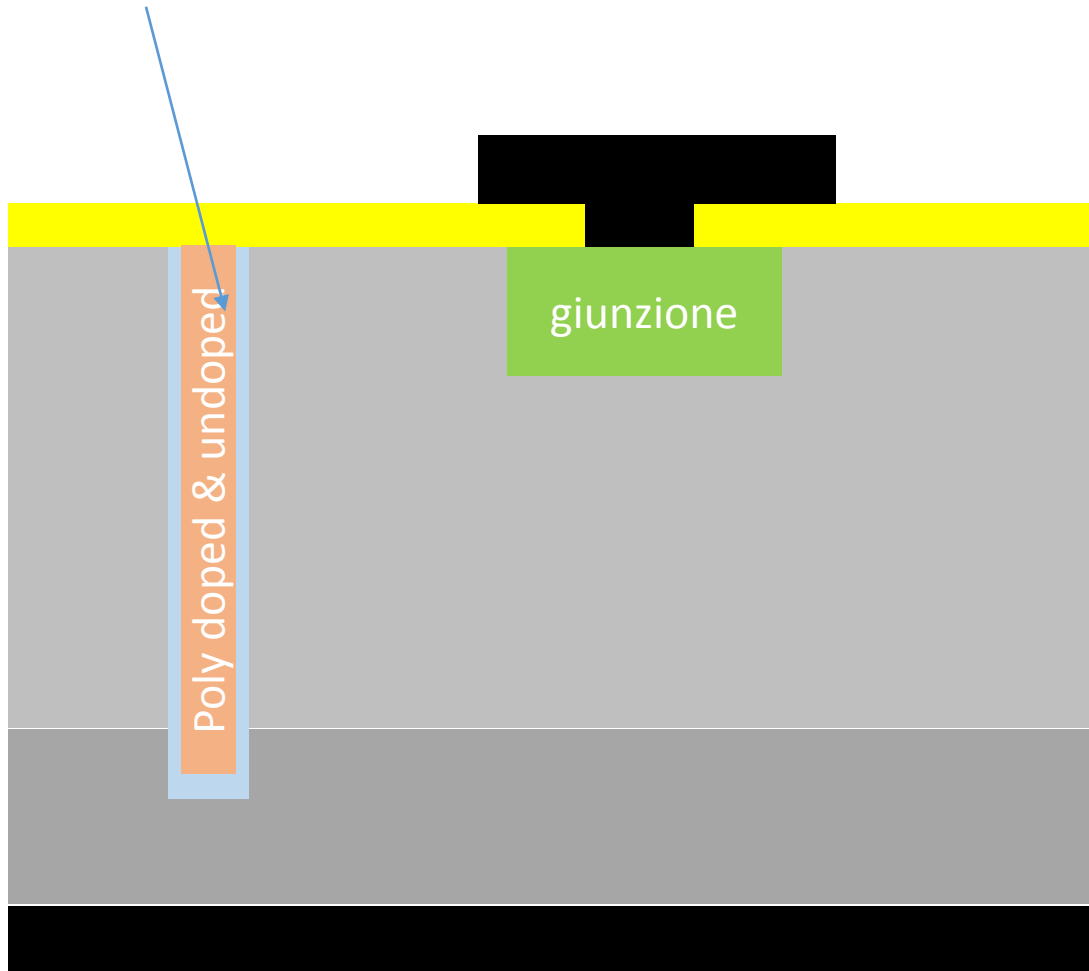
Molti dispositivi SENZA bordo attivo



Evitare incroci di trench, sull'incrocio il trench si può «allargare»

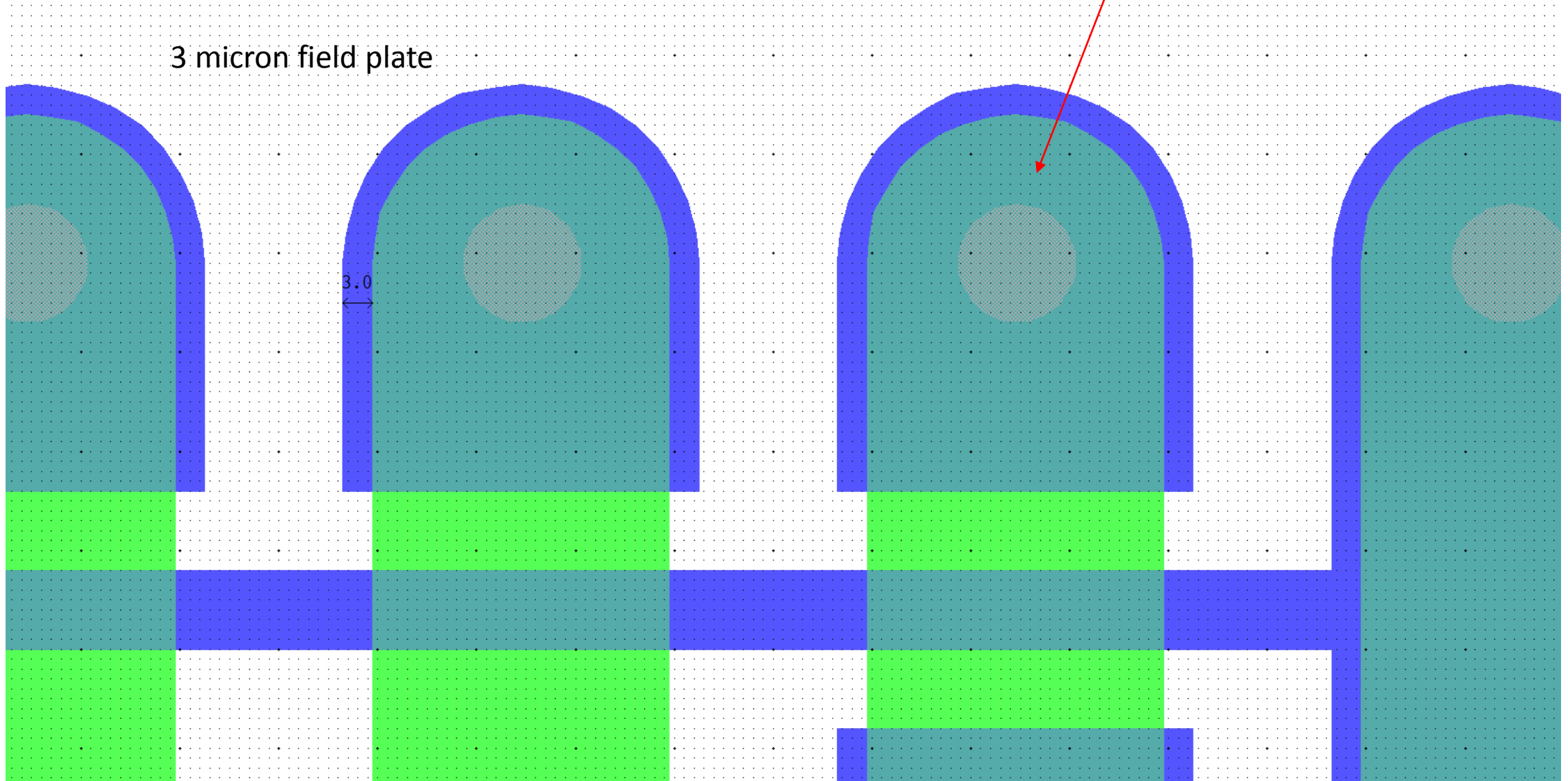
- Nel processo non esiste un livello p+ «planare»
- processo SENZA tappo nei Si-3D

Contatto ohmico



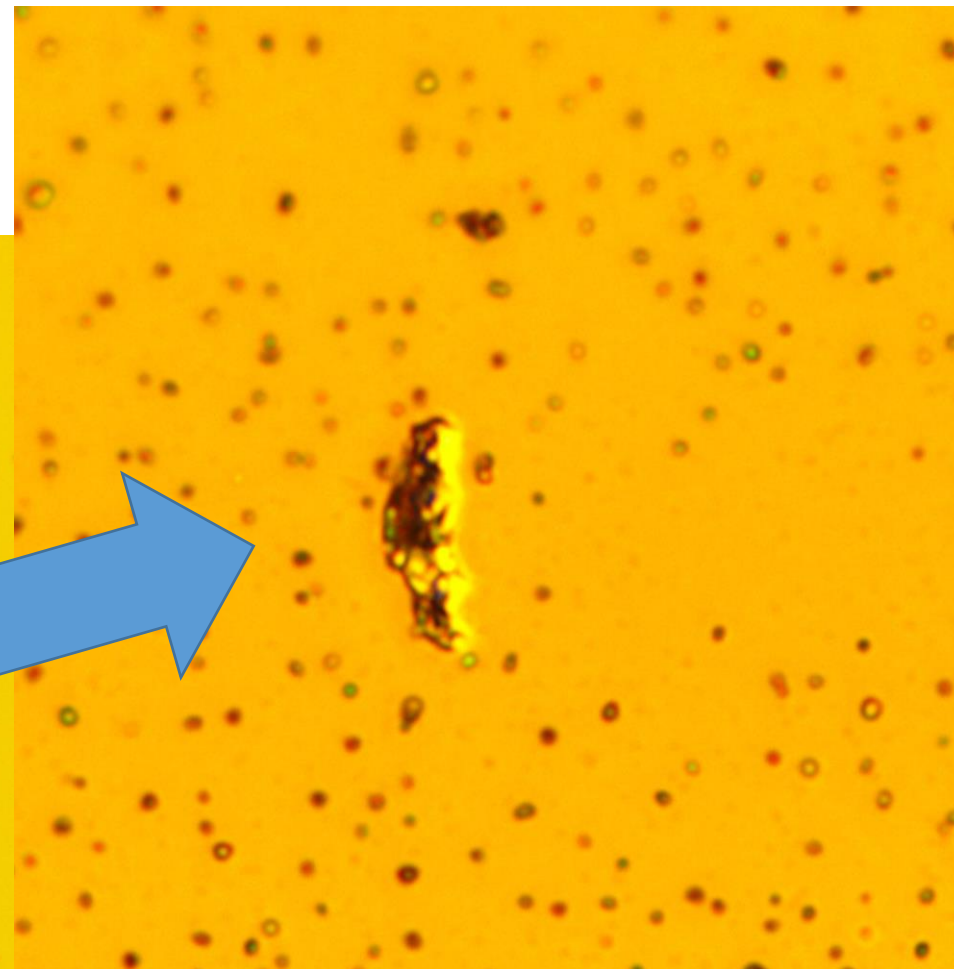
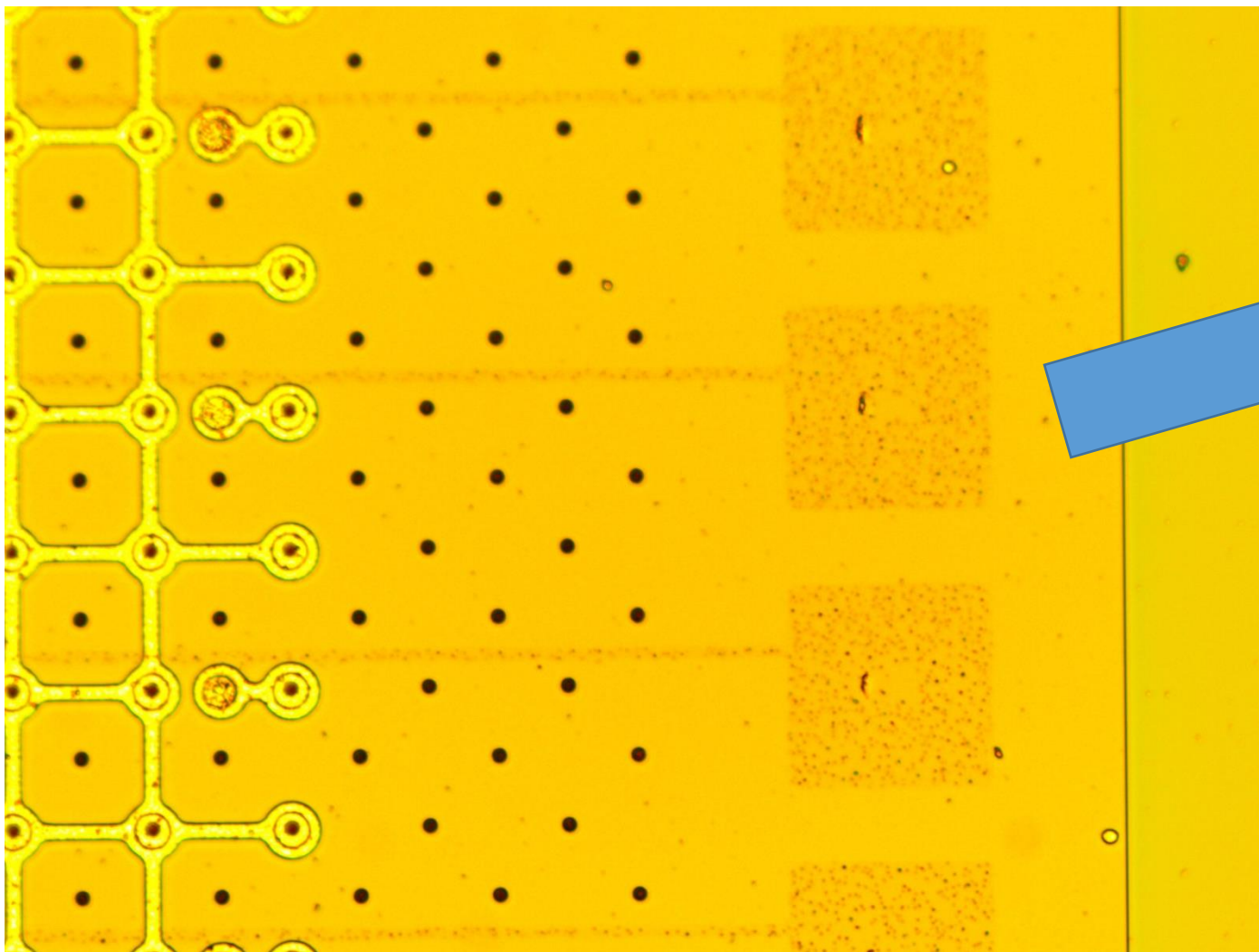


Su ogni apertura per il bump DEVE esserci la metal temporanea



METAL TEMPORANEA:

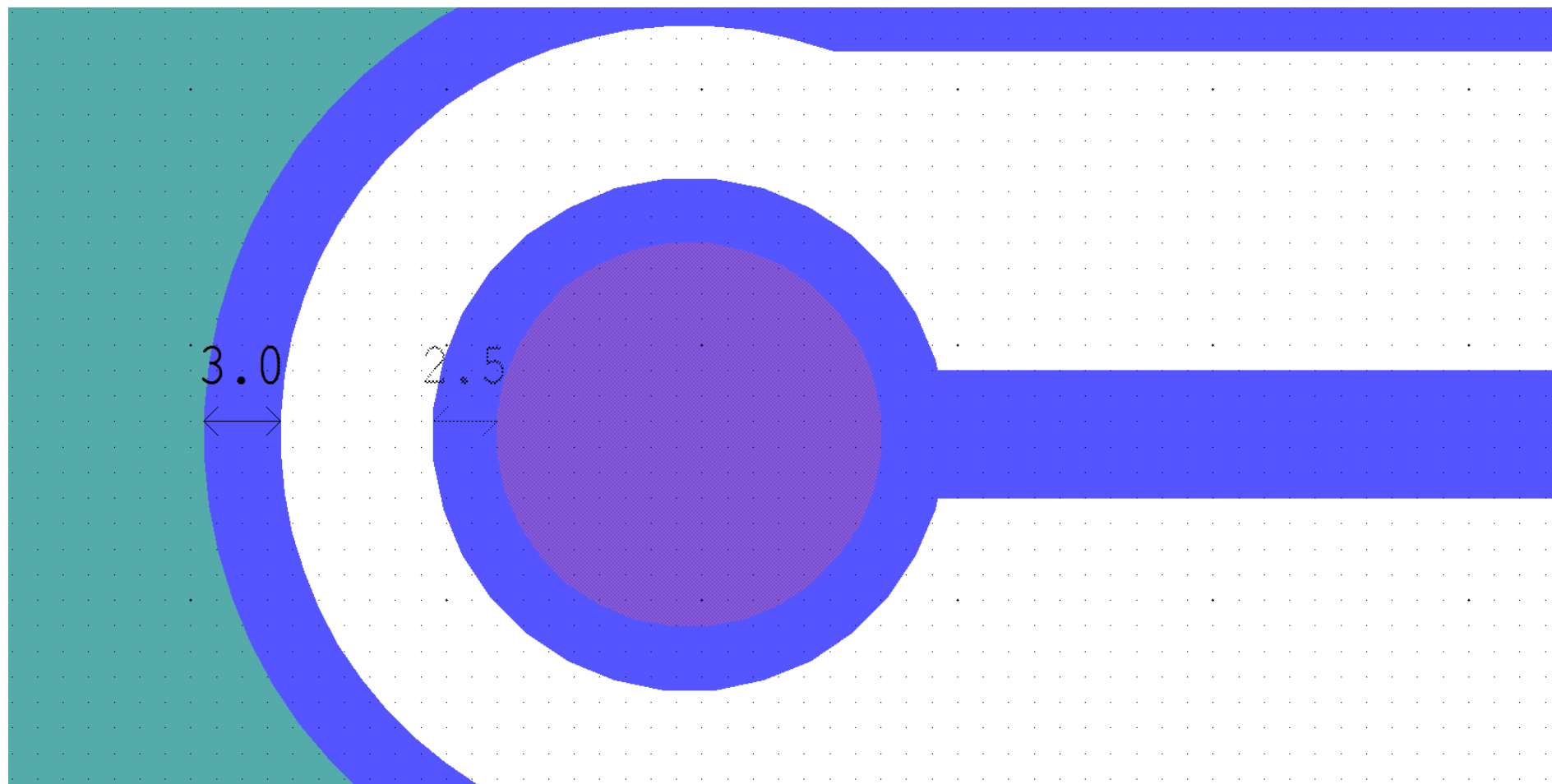
- Residui di silicio e di metallo
- Non c'è evidenza di «incisioni» nell'ossido

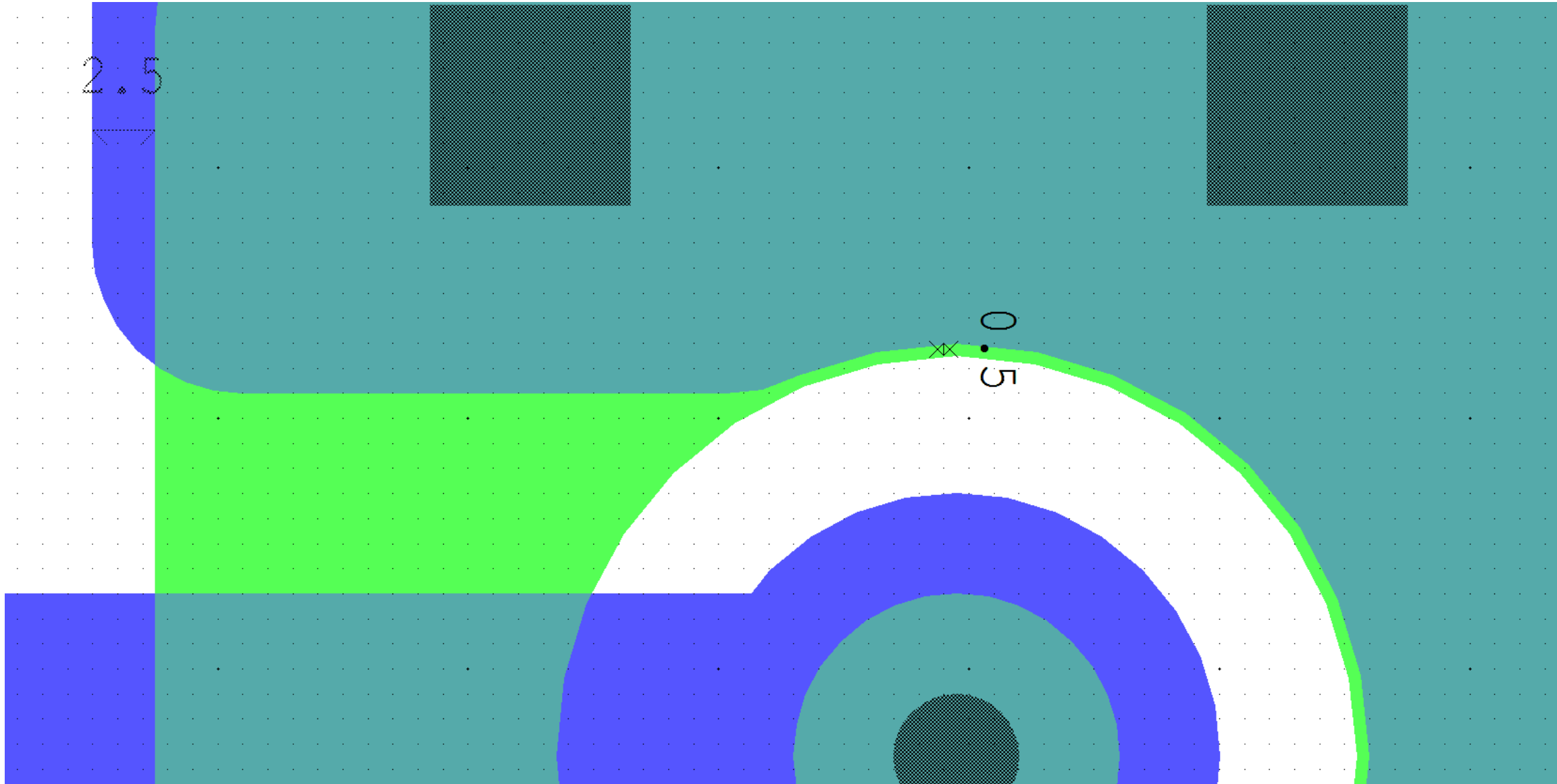


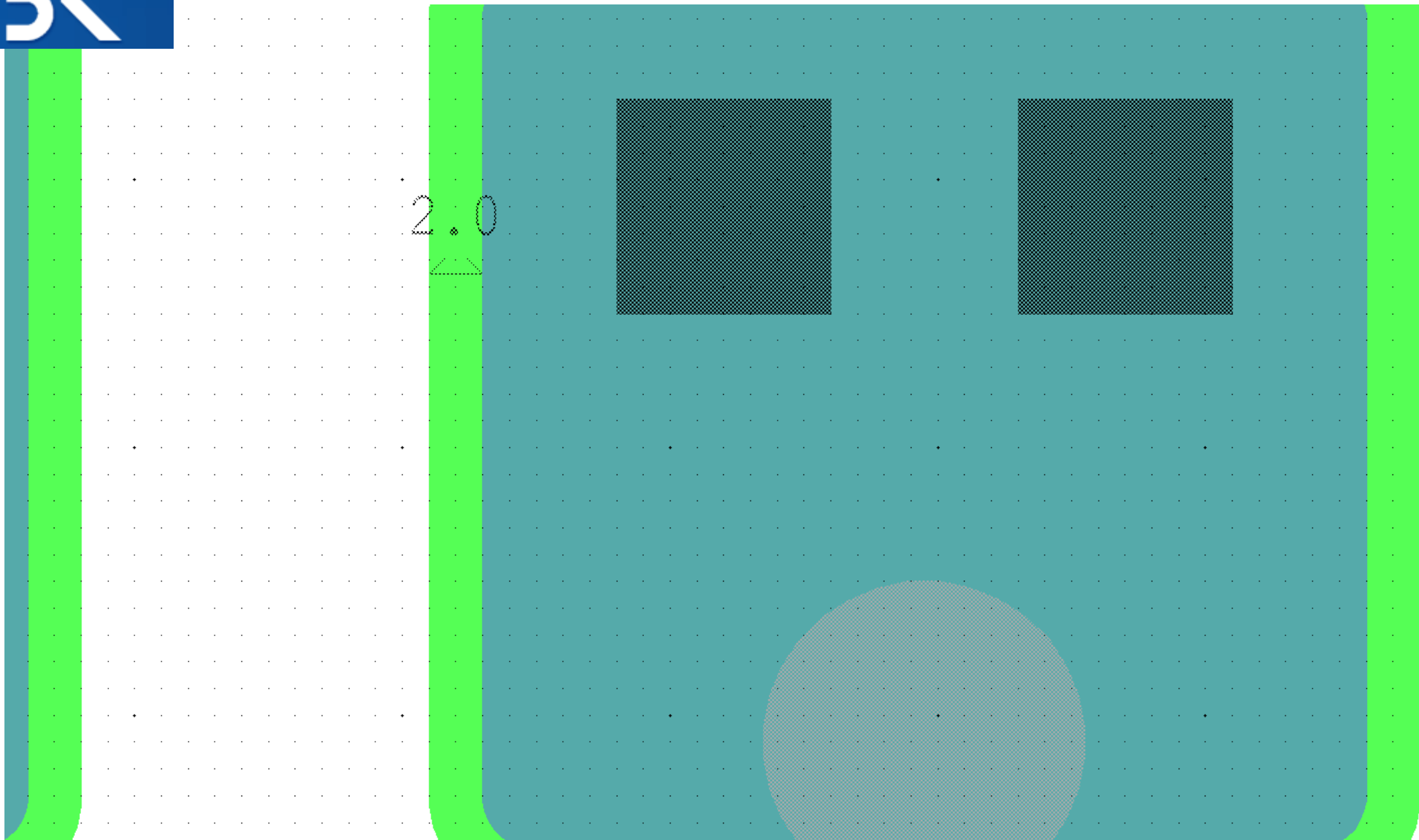


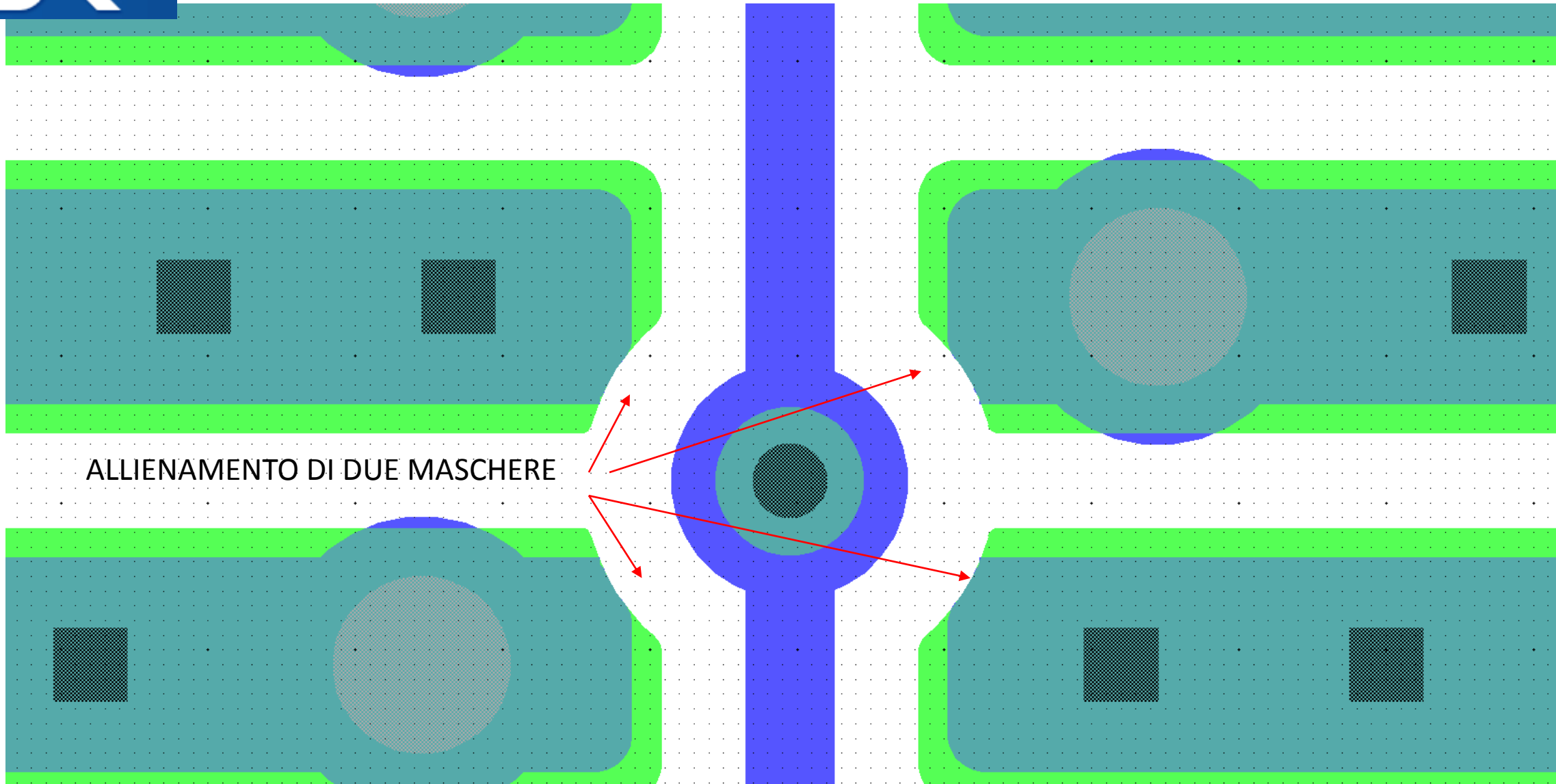
IN GENERALE SOTTO I 4 MICRON CI SONO RISCHI DOVUTI A:

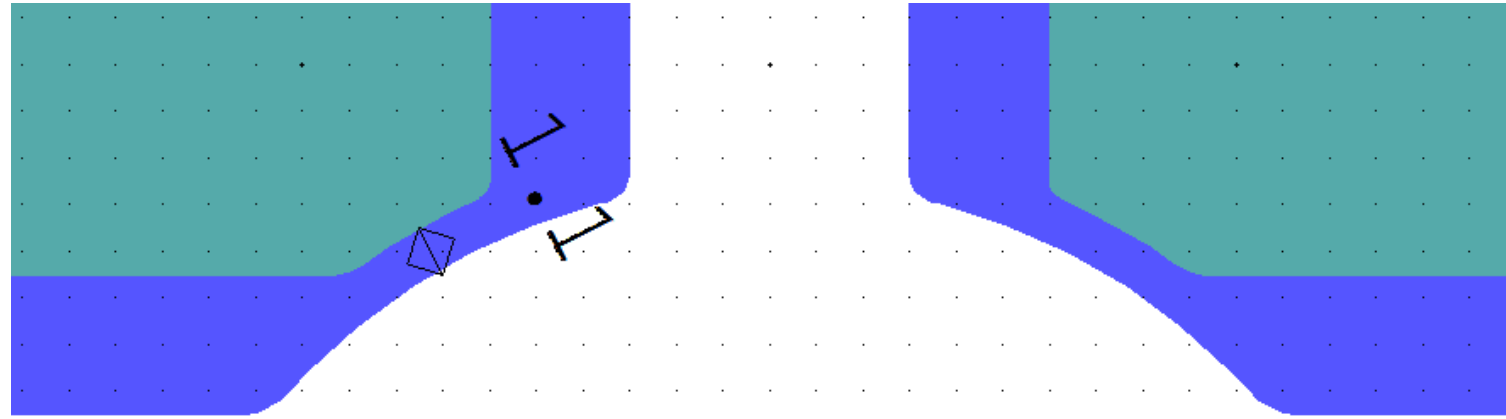
- **DEFINIZIONE**
- **ALLINEAMENTO**



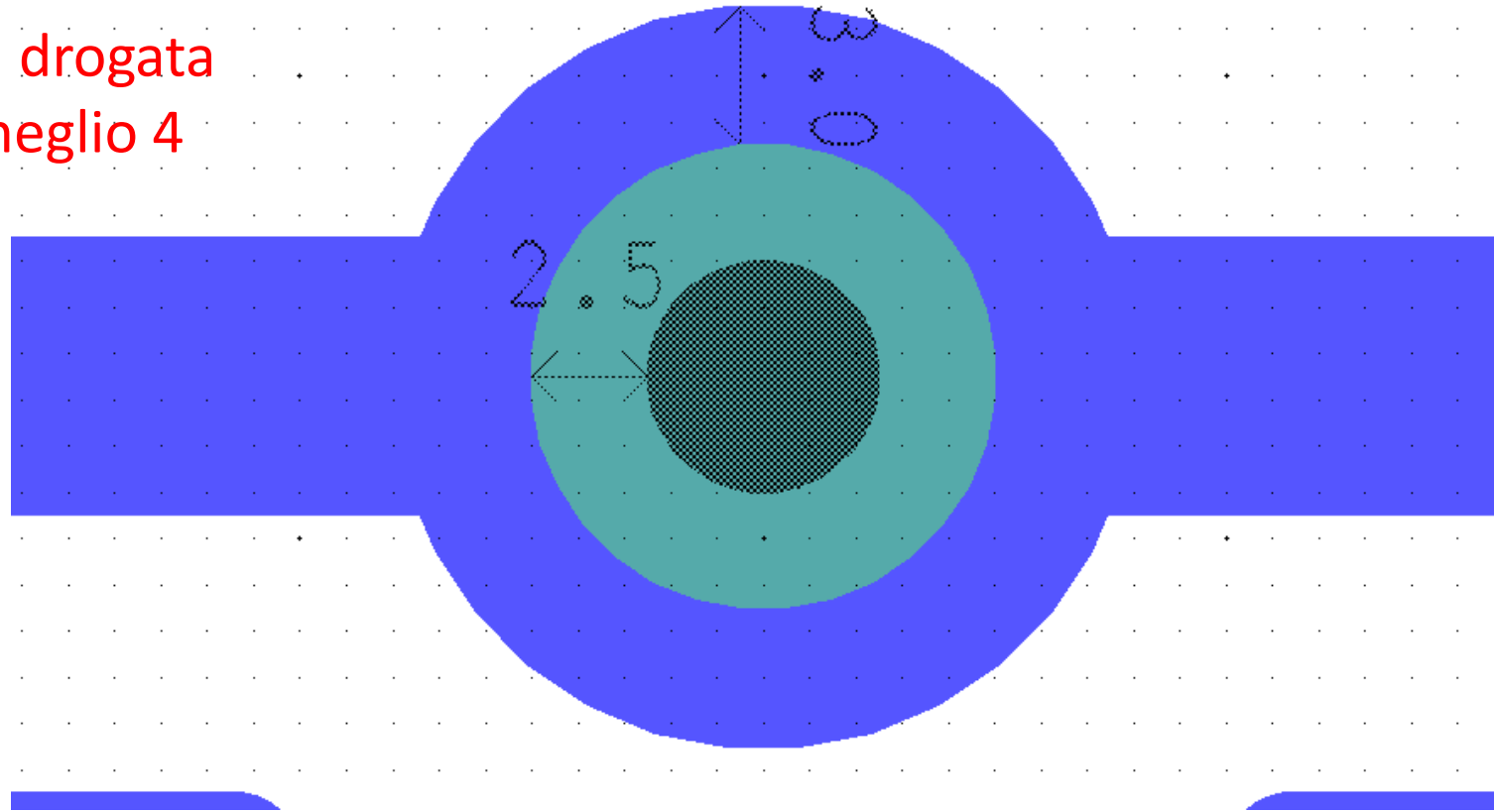








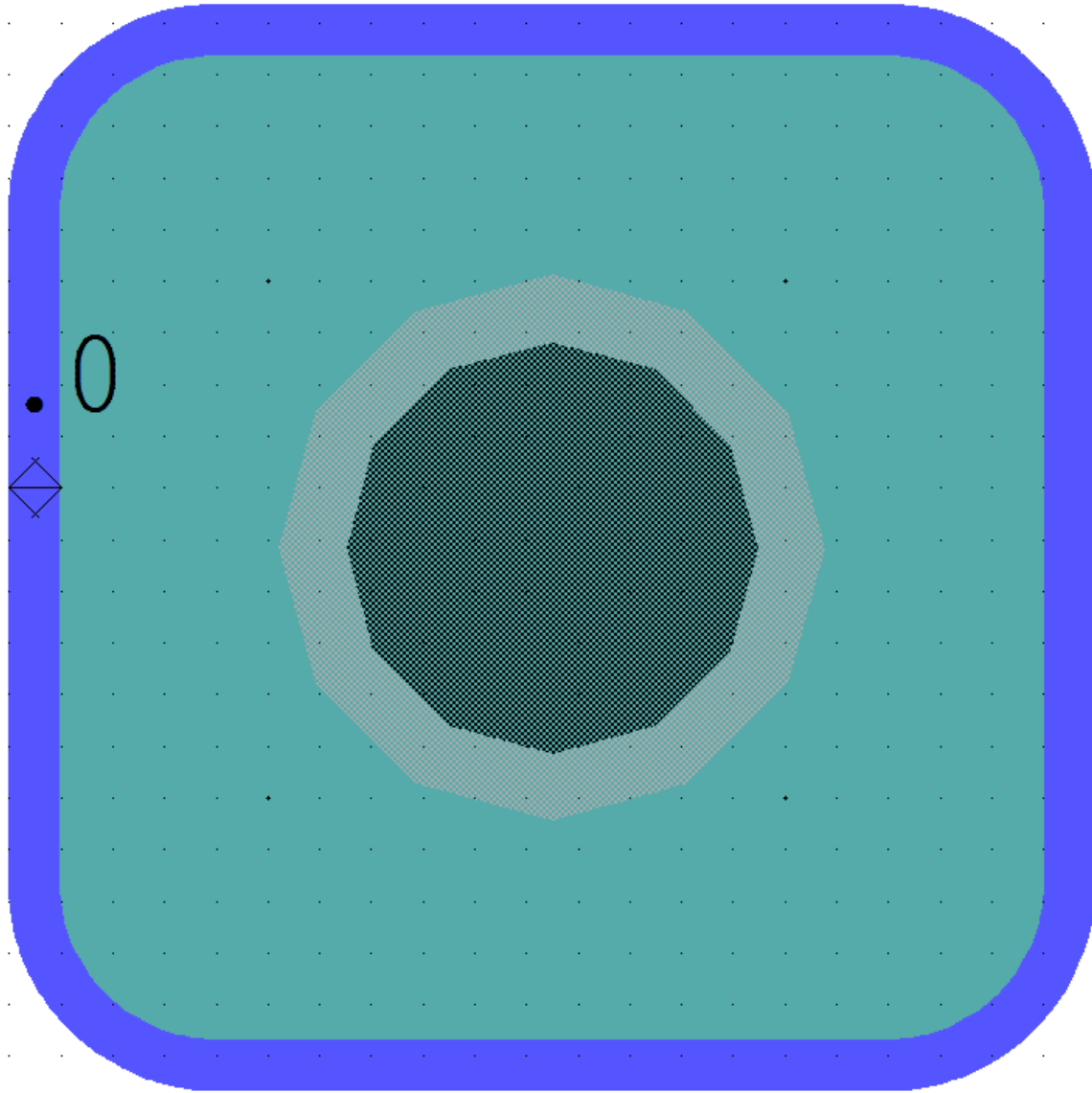
Distanza contatto \ zona drogata
non meno di 3 micron meglio 4





CLIC ??

1.0



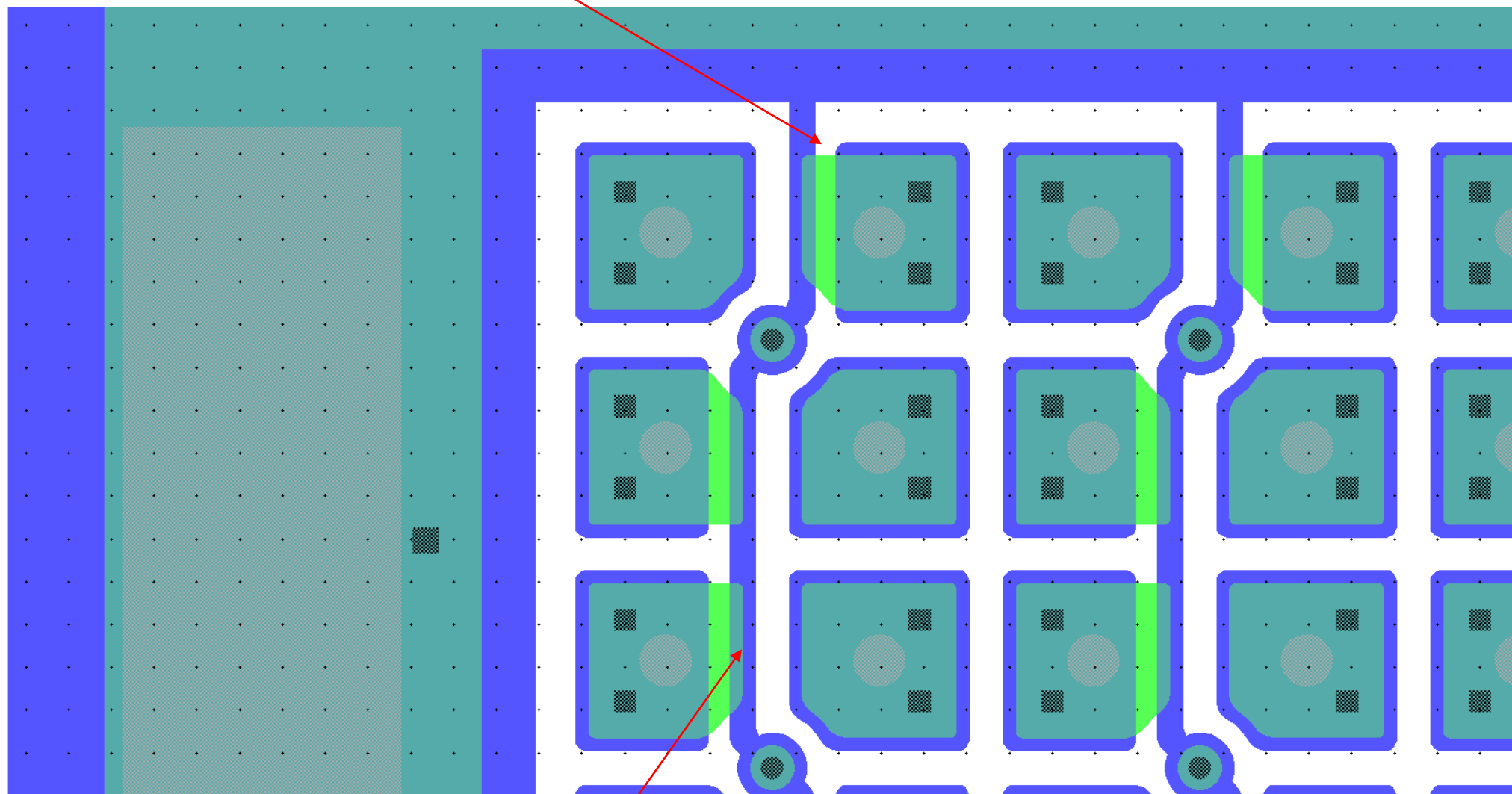


AREA DI CONTATTO UNIFORME;
VA SOSTITUITA CON UNA MATRICE DI CONTATTI





Rischio di corti metallici



Rischio pinhole



Solo una curiosità, perché questa struttura ?

